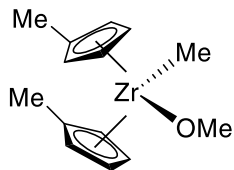


Catalog # 40-1028 Bis(methylcyclopentadienyl)(methyl)(methoxy)zirconium(IV), 98+%



Thermal Behavior:

- TGA diagram and data is available in [1, 2]

Technical Notes:

- ALD/CVD precursor for zirconium containing thin film deposition.

Target Deposit	Deposition Technique	Delivery Temperature	Pressure	Co-reactants	Deposition Temperature	Ref.
ZrO ₂	ALD	160°C	3.75 Torr	H ₂ O	350-650°C	1
	CVD	Tol. Solution		O ₂	250-450°C	1
	ALD	68°C	1.5-2.25 Torr	H ₂ O	300-500°C	3
	ALD	68°C	1.5-2.25 Torr	O ₃	250-500°C	4
M ₂ O ₃ :ZrO ₂ M=La, Hf, Er, Gd	ALD	160°C	3.75 Torr	(ⁱ PrCp) ₃ La, H ₂ O	300°C	5
	ALD	68°C	1.5-2.25 Torr	(CpMe) ₂ Hf(OMe)Me, O ₃	350°C	6
	ALD	-	-	Er(thd) ₃ , Gd(thd) ₃ O ₃	350°C	7, 8

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